

Amendments to the Claims:

This listing of claims reflects all claim amendments and replaces all prior versions, and listings, of claims in the application. Material to be inserted is in **bold and underline**, and material to be deleted is in ~~strikeout~~ or in [[double brackets]] if the deletion would be difficult to see.

LISTING OF CLAIMS:

1. (Currently amended) A method for making a tandem thin-film photoelectric converter comprising a transparent electrode layer, at least one amorphous silicon photoelectric conversion unit, at least one crystalline silicon photoelectric conversion unit, and a back electrode layer stacked in that order on a transparent insulating substrate, the method comprising a step of forming the back electrode layer by the method for making a transparent conductive film comprising introducing an organozinc compound and a mixed gas in which an oxidizing agent is diluted with a hydrogen gas, into a deposition chamber to form a transparent conductive film containing zinc oxide as a main component on a substrate disposed in the deposition chamber, the transparent insulating substrate being used as the substrate, **wherein a temperature of the substrate is from 50°C to 300°C and a pressure in the deposition chamber is from 0.01 to 3 Torr.**
2. (Original) The method for making the transparent conductive film according to Claim 1, wherein the organozinc compound is diethylzinc.
3. (Original) The method for making the transparent conductive film according to Claim 1, wherein the oxidizing agent is water.

4. (Original) The method for making the transparent conductive film according to Claim 1, wherein a Group III element-containing compound is introduced into the deposition chamber so that the transparent conductive film containing zinc oxide as the main component doped with a small amount of the Group III element is formed on the substrate.

5. (Currently amended) The method for making the transparent conductive film according to Claim 4, wherein the Group III element-containing compound is at least one of diborane (B_2H_6) (B_2H_6) and trimethylaluminum ($(CH_3)_3Al$) ($(CH_3)_3Al$).

6. (Cancelled)

7. (Currently amended) A method for making a tandem thin-film photoelectric converter comprising a transparent electrode layer, at least one amorphous silicon photoelectric conversion unit, at least one crystalline silicon photoelectric conversion unit, and a back electrode layer stacked in that order on a transparent insulating substrate, the method comprising a step of forming the transparent electrode layer by the method for making a transparent conductive film comprising introducing an organozinc compound and a mixed gas in which an oxidizing agent is diluted with a hydrogen gas, into a deposition chamber to form a transparent conductive film containing zinc oxide as a main component on a substrate disposed in the deposition chamber, the transparent insulating substrate being used as the substrate, wherein a temperature of the substrate is from

50°C to 300°C and a pressure in the deposition chamber is from 0.01 to 3 Torr.

8. (Previously presented) The method for making the transparent conductive film according to Claim 7, wherein the organozinc compound is diethylzinc.

9. (Previously presented) The method for making the transparent conductive film according to Claim 7, wherein the oxidizing agent is water.

10. (Previously presented) The method for making the transparent conductive film according to Claim 7, wherein a Group III element-containing compound is introduced into the deposition chamber so that the transparent conductive film containing zinc oxide as the main component doped with a small amount of the Group III element is formed on the substrate.

11. (Previously presented) The method for making the transparent conductive film according to Claim 10, wherein the Group III element-containing compound is at least one of diborane (B_2H_6) and trimethylaluminum ($(CH_3)_3Al$).